

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S33	160	(gate adj1 (dielectric insulat\$3)) with sacrif\$5 with (electrode metal storage).bi.	US-PGPUB; USPAT	OR	ON	2005/11/08 10:31
S34	3	S33 and MIM	US-PGPUB; USPAT	OR	ON	2005/11/08 10:29
S35	1629	sacrif\$5 with (metal electrode) with (dielectric insulat\$3).bi.	US-PGPUB; USPAT	OR	ON	2005/11/08 12:47
S36	8	S35 same MIM	US-PGPUB; USPAT	OR	ON	2005/11/08 13:20
S37	6	"500580".ap.	US-PGPUB; USPAT	OR	ON	2005/11/08 14:39
S38	0	(chochralski with grow\$3 with (silicon adj crystal)).bi.	US-PGPUB; USPAT	OR	ON	2005/11/08 14:41
S39	2	(chochralski with grow\$3 with (silicon with crystal)).bi.	US-PGPUB; USPAT	OR	ON	2005/11/08 14:43
S40	5	(chochralski with grow\$3 with (silicon crystal)).bi.	US-PGPUB; USPAT	OR	ON	2005/11/08 14:47
S41	857	((CZ chochralski) with grow\$3 with (silicon crystal)).bi.	US-PGPUB; USPAT	OR	ON	2005/11/08 14:47
S42	584	((CZ chochralski) adj1 (method process technique)) with grow\$3 with (silicon crystal).bi.	US-PGPUB; USPAT	OR	ON	2005/11/09 10:14
S43	123	((CZ chochralski) adj1 (method process technique)) with grow\$3 with (silicon crystal) with (defect vacancies).bi.	US-PGPUB; USPAT	OR	ON	2005/11/08 15:09
S44	243	((CZ czochralski) adj1 (method process technique)) with grow\$3 with (silicon crystal) with (defect vacancies).bi.	US-PGPUB; USPAT	OR	ON	2005/11/09 09:27
S45	121	S44 not S43	US-PGPUB; USPAT	OR	ON	2005/11/08 15:10
S46	243	((CZ czochralski) adj1 (method process technique)) with grow\$3 with (silicon crystal) with (defect vacancies).bi.	US-PGPUB; USPAT	OR	ON	2005/11/09 09:27
S47	2	S46 and (SOI with silicon with crystal with (N adj1 region))	US-PGPUB; USPAT	OR	ON	2005/11/09 10:15
S49	1622	((CZ MCZ czochralski) adj1 (method process technique)) with grow\$3 with (silicon crystal).bi.	US-PGPUB; USPAT	OR	ON	2005/11/09 10:15
S50	2	S49 and (SOI with silicon with crystal with (N adj1 region))	US-PGPUB; USPAT	OR	ON	2005/11/09 10:16